

AMENDMENTS TO THE ABSTRACT:

Please replace the abstract with the following amended abstract:

Provided is a method of depositing a thin film using a hafnium compound. ~~In this~~  
~~The method, the depositing (S200) of a thin film~~ includes (S20) depositing a primary thin  
 film and (S21) depositing a secondary thin film. ~~Step (S200) is performed by repeating~~  
~~steps (S20) and (S21)~~The depositing of the primary thin film and the depositing of the  
secondary thin film are repeated once or more. ~~Step (S20)~~The depositing of the primary  
thin film includes ~~(S20-1)~~ feeding a first reactive gas, ~~(S20-2)~~ purging the first reactive  
 gas, ~~(S20-3)~~ feeding a third reactive gas, and ~~(S20-4)~~ purging the third reactive gas, and  
repeats the steps N times. The feeding of the first reactive gas ~~Step (S21)~~ includes ~~(S21-~~  
~~1)~~ feeding a second reactive gas, ~~(S21-2)~~ purging the second reactive gas, ~~(S21-3)~~  
 feeding the third reactive gas, and ~~(S21-4)~~ purging the third reactive gas, and repeats the  
steps. ~~Step (S20) is performed by repeating steps (S20-1), (S20-2), (S20-3), and (S20-4)~~  
 N times, and ~~step (S21) is performed by repeating steps (S21-1), (S21-2), (S21-3), and~~  
 (S21-4) M times.